

## Low VF Current Density Surface Mount Schottky Barrier Rectifiers

### Major Ratings and Characteristics

$I_{F(AV)}$	2 A
$V_{RRM}$	20 V, 30 V
$I_{FSM}$	50 A
$E_{AS}$	11.25 mJ
$V_F$	0.45 V
$T_j$ max.	150 °C



DO-220AA (SMP)

### Features

- Very low profile - typical height of 1.0mm
- Ideal for automated placement
- Low forward voltage drop, low power losses
- High efficiency
- Low thermal resistance
- Meets MSL level 1, per J-STD-020C
- AEC-Q101 qualified

### Typical Applications

For use in low voltage high frequency inverters, free-wheeling, dc-to-dc converters, and polarity protection applications

### Mechanical Data

**Case:** DO-220AA (SMP)

Epoxy meets UL-94V-0 Flammability rating

**Terminals:** Matte Tin plated (E3 Suffix) leads, solderable per J-STD-002B and MIL-STD-750, Method 2026

**Polarity:** Color band denotes the cathode end

### Maximum Ratings

$T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	SS2P2L	SS2P3L	Unit
Device marking code		22L	23L	
Maximum repetitive peak reverse voltage	$V_{RRM}$	20	30	V
RMS reverse voltage	$V_{RWM}$	14	21	V
DC blocking voltage	$V_R$	20	30	V
Maximum average forward rectified current see Fig. 1	$I_{F(AV)}$	2.0		A
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	$I_{FSM}$	50		A
Non-repetitive avalanche energy at $I_{AS} = 1.5\text{ A}$ , $L = 10\text{ mH}$ , $T_J = 25\text{ °C}$	$E_{AS}$	11.25		mJ
Voltage rate of change (rated $V_R$ )	$dv/dt$	10000		V/us
Operating junction and storage temperature range	$T_J, T_{STG}$	-55 to +150		°C

### Electrical Characteristics

$T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Test condition	Symbol	Typ	Max.	Unit
Maximum instantaneous forward voltage <sup>(1)</sup>	at $I_F = 2\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	$V_F$	0.45	0.50	V
	at $I_F = 2\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		0.38	0.45	
Maximum reverse current at rated VRM <sup>(1)</sup>	$T_J = 25\text{ }^\circ\text{C}$	$I_R$	-	200	$\mu\text{A}$
	$T_J = 125\text{ }^\circ\text{C}$		9.0	20	mA
Typical junction capacitance	at 4.0 V, 1 MHz	$C_J$	130		pF

**Note:**

(1) Pulse test: 300 $\mu\text{s}$  pulse width, 1% duty cycle

### Thermal Characteristics

$T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	SS2P2L	SS2P3L	Unit
Typical thermal resistance <sup>(1)</sup>	$R_{\theta JA}$	115		$^\circ\text{C/W}$
	$R_{\theta JL}$	15		
	$R_{\theta JC}$	20		

**Note:**

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0mm copper pad areas.  $R_{\theta JL}$  is measured at the terminal of cathode band.  $R_{\theta JC}$  is measured at the top centre of the body

## Ratings and Characteristics Curves

( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise specified)

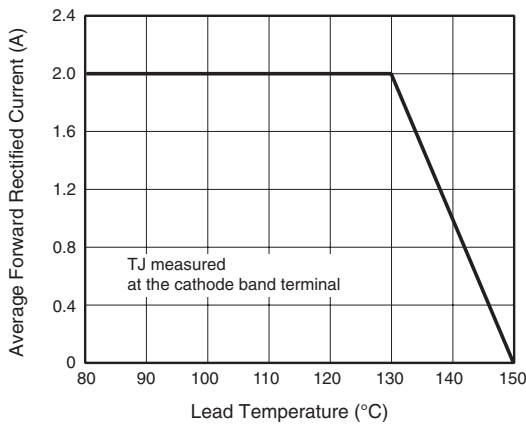


Figure 1. Forward Current Derating Curve

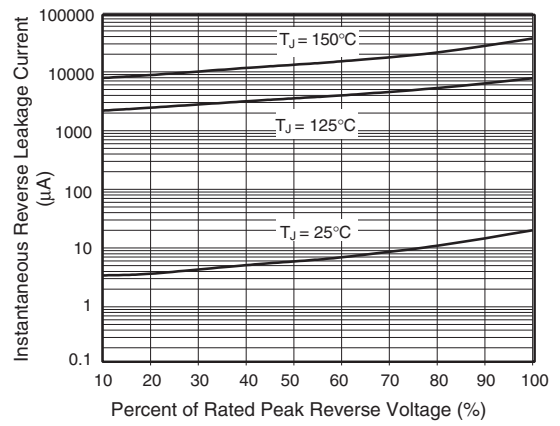


Figure 4. Typical Reverse Leakage Characteristics

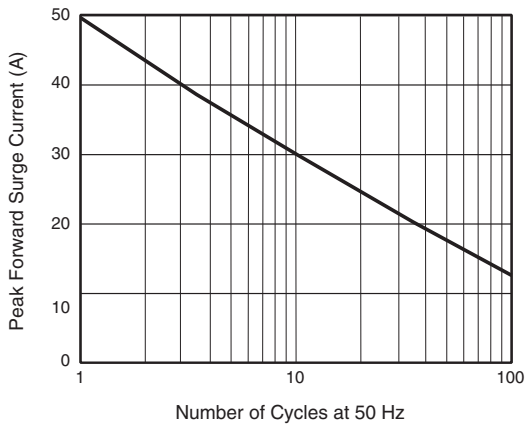


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

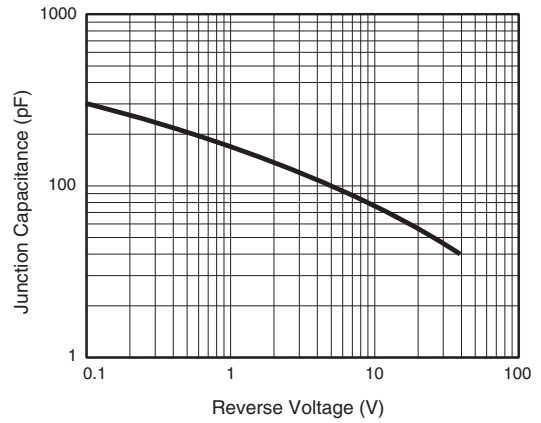


Figure 5. Typical Junction Capacitance

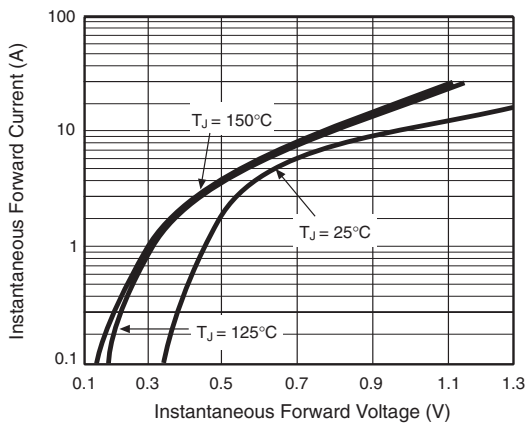


Figure 3. Typical Instantaneous Forward Characteristics

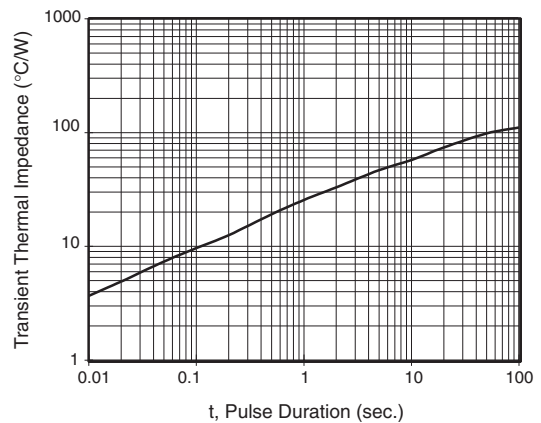


Figure 6. Typical Transient Thermal impedance

## Package Dimensions in Inches (millimeters)

DO-220AA (SMP)

